

## Selection Guide

		7C10211B-10	7C1021B-12	7C1021B-15
Maximum Access Time (ns)		10	12	15
Maximum Operating Current (mA)	Com'I / Ind'I	150	140	130
	Automotive-A			130
	Automotive-E			130
Maximum CMOS Standby Current (mA)	Com'I / Ind'I	10	10	10
	Com'I / Ind'I (L version)	0.5	0.5	0.5
	Automotive-A (L version)			0.5
	Automotive-E			15

## Pin Definitions

Pin Name	SOJ, TSOP-Pin Number	I/O Type	Description
A <sub>0</sub> -A <sub>15</sub>	1-5, 18-21, 24-27, 42-44	Input	<b>Address Inputs used to select one of the address locations.</b>
I/O <sub>1</sub> -I/O <sub>16</sub>	7-10, 13-16, 29-32, 35-38	Input/Output	<b>Bidirectional Data I/O lines.</b> Used as input or output lines depending on operation.
NC	22, 23, 28	No Connect	<b>No Connects.</b> Not connected to the die.
$\overline{WE}$	17	Input/Control	<b>Write Enable Input, active LOW.</b> When selected LOW, a Write is conducted. When deselected HIGH, a Read is conducted.
$\overline{CE}$	6	Input/Control	<b>Chip Enable Input, active LOW.</b> When LOW, selects the chip. When HIGH, deselects the chip.
$\overline{BHE}$ , $\overline{BLE}$	40, 39	Input/Control	<b>Byte Write Select Inputs, active LOW.</b> $\overline{BHE}$ controls I/O <sub>16</sub> -I/O <sub>9</sub> , $\overline{BLE}$ controls I/O <sub>8</sub> -I/O <sub>1</sub> , .
$\overline{OE}$	41	Input/Control	<b>Output Enable, active LOW.</b> Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are tri-stated, and act as input data pins.
V <sub>SS</sub>	12, 34	Ground	<b>Ground for the device.</b> Should be connected to ground of the system.
V <sub>CC</sub>	11, 33	Power Supply	<b>Power Supply inputs to the device.</b>

## Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... -65°C to +150°C

Ambient Temperature with  
Power Applied ..... -55°C to +125°C

Supply Voltage on  $V_{CC}$  Relative to GND<sup>[2]</sup> .... -0.5V to +7.0V

DC Voltage Applied to Outputs  
in High Z State<sup>[2]</sup> ..... -0.5V to  $V_{CC}+0.5V$

DC Input Voltage<sup>[2]</sup> ..... -0.5V to  $V_{CC}+0.5V$

Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V  
(per MIL-STD-883, Method 3015)

Latch-Up Current ..... >200 mA

## Operating Range

Range	Ambient Temperature ( $T_A$ ) <sup>[3]</sup>	$V_{CC}$
Commercial	0°C to +70°C	5V ± 10%
Industrial	-40°C to +85°C	
Automotive-A	-40°C to +85°C	
Automotive-E	-40°C to +125°C	

## Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		-10		-12		-15		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = −4.0 mA		2.4		2.4		2.4		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 8.0 mA			0.4		0.4		0.4	V
V <sub>IH</sub>	Input HIGH Voltage			2.2	6.0	2.2	6.0	2.2	6.0	V
V <sub>IL</sub>	Input LOW Voltage <sup>[2]</sup>			−0.5	0.8	−0.5	0.8	−0.5	0.8	V
I <sub>IX</sub>	Input Leakage Current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub>	Com'l / Ind'l	−1	+1	−1	+1	−1	+1	μA
			Automotive-A					−1	+1	μA
			Automotive-E					−4	+4	μA
I <sub>OZ</sub>	Output Leakage Current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub> , Output Disabled	Com'l / Ind'l	−1	+1	−1	+1	−1	+1	μA
			Automotive-A					−1	+1	μA
			Automotive-E					−4	+4	μA
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max., I <sub>OUT</sub> = 0 mA, f = f <sub>MAX</sub> = 1/t <sub>RC</sub>	Com'l / Ind'l		150		140		130	mA
			Automotive-A						130	
			Automotive-E						130	
I <sub>SB1</sub>	Automatic CE Power-Down Current—TTL Inputs	Max. V <sub>CC</sub> , CE ≥ V <sub>IH</sub> V <sub>IN</sub> ≥ V <sub>IH</sub> or V <sub>IN</sub> ≤ V <sub>IL</sub> , f = f <sub>MAX</sub>	Com'l / Ind'l		40		40		40	mA
			Automotive-A						40	
			Automotive-E						50	
I <sub>SB2</sub>	Automatic CE Power-Down Current—CMOS Inputs	Max. V <sub>CC</sub> , CE ≥ V <sub>CC</sub> − 0.3V, V <sub>IN</sub> ≥ V <sub>CC</sub> − 0.3V, or V <sub>IN</sub> ≤ 0.3V, f = 0	Com'l / Ind'l		10		10		10	mA
			Com'l / Ind'l (L)		0.5		0.5		0.5	
			Automotive-A (L)						0.5	
			Automotive-E						15	

## Capacitance<sup>[4]</sup>

Parameter	Description	Test Conditions	Max.	Unit
$C_{IN}$	Input Capacitance	$T_A = 25^\circ\text{C}, f = 1 \text{ MHz}, V_{CC} = 5.0V$	8	pF
$C_{OUT}$	Output Capacitance		8	pF

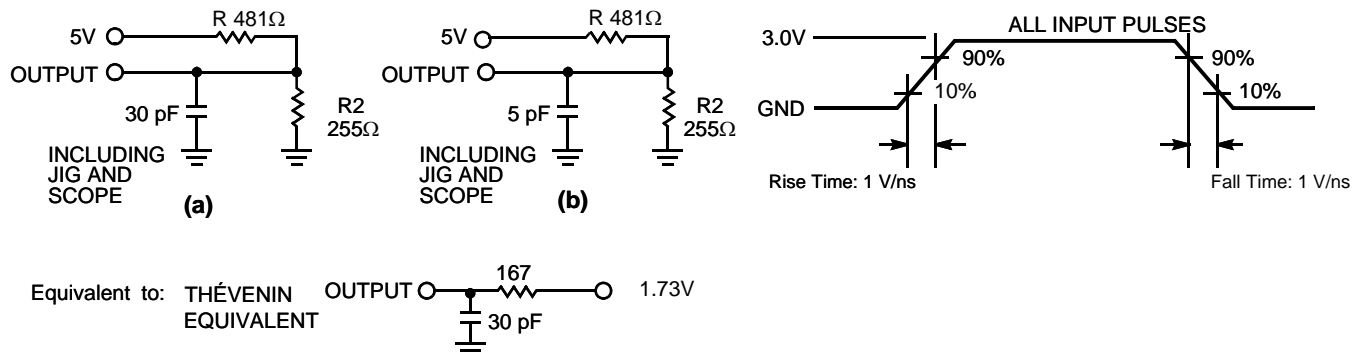
### Notes:

- $V_{IL}(\text{min.}) = -2.0V$  and  $V_{IH}(\text{max.}) = V_{CC} + 0.5V$  for pulse durations of less than 20 ns.
- $T_A$  is the "Instant On" case temperature.
- Tested initially and after any design or process changes that may affect these parameters.

## Thermal Resistance<sup>[4]</sup>

Parameter	Description	Test Conditions	44-pin SOJ	44-pin TSOP-II	Unit
$\Theta_{JA}$	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA / JESD51.	64.32	76.89	°C/W
$\Theta_{JC}$	Thermal Resistance (Junction to Case)		31.03	14.28	°C/W

## AC Test Loads and Waveforms



## Switching Characteristics<sup>[5]</sup> Over the Operating Range

Parameter	Description	7C10211B-10		7C1021B-12		7C1021B-15		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle								
t <sub>RC</sub>	Read Cycle Time	10		12		15		ns
t <sub>AA</sub>	Address to Data Valid		10		12		15	ns
t <sub>OHA</sub>	Data Hold from Address Change	3		3		3		ns
t <sub>ACE</sub>	$\overline{CE}$ LOW to Data Valid		10		12		15	ns
t <sub>DOE</sub>	$\overline{OE}$ LOW to Data Valid		5		6		7	ns
t <sub>LZOE</sub>	$\overline{OE}$ LOW to Low Z <sup>[6]</sup>	0		0		0		ns
t <sub>HZOE</sub>	$\overline{OE}$ HIGH to High Z <sup>[6, 7]</sup>		5		6		7	ns
t <sub>LZCE</sub>	$\overline{CE}$ LOW to Low Z <sup>[6]</sup>	3		3		3		ns
t <sub>HZCE</sub>	$\overline{CE}$ HIGH to High Z <sup>[6, 7]</sup>		5		6		7	ns
t <sub>PU</sub>	$\overline{CE}$ LOW to Power-Up	0		0		0		ns
t <sub>PD</sub>	$\overline{CE}$ HIGH to Power-Down		10		12		15	ns
t <sub>DBE</sub>	Byte Enable to Data Valid		5		6		7	ns
t <sub>LZBE</sub>	Byte Enable to Low Z	0		0		0		ns
t <sub>HZBE</sub>	Byte Disable to High Z		5		6		7	ns

### Notes:

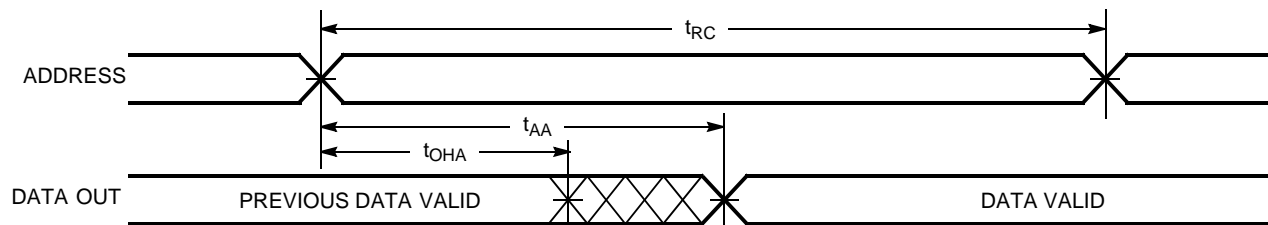
- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified  $I_{OL}/I_{OH}$  and 30-pF load capacitance.
- At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any given device.
- $t_{HZOE}$ ,  $t_{HZBE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured  $\pm 500$  mV from steady-state voltage.

## Switching Characteristics<sup>[5]</sup> Over the Operating Range (continued)

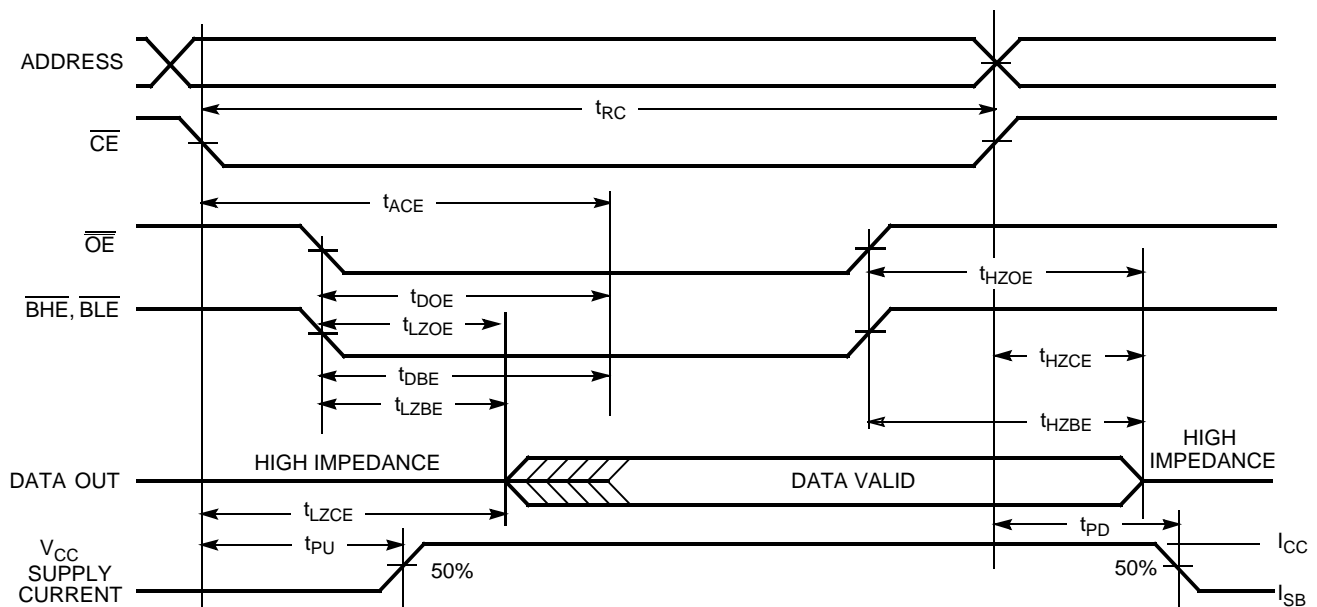
Parameter	Description	7C10211B-10		7C1021B-12		7C1021B-15		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Write Cycle <sup>[8]</sup>								
t <sub>WC</sub>	Write Cycle Time	10		12		15		ns
t <sub>SCE</sub>	CE LOW to Write End	8		9		10		ns
t <sub>AW</sub>	Address Set-Up to Write End	7		8		10		ns
t <sub>HA</sub>	Address Hold from Write End	0		0		0		ns
t <sub>SA</sub>	Address Set-Up to Write Start	0		0		0		ns
t <sub>SD</sub>	Data Set-Up to Write End	5		6		8		ns
t <sub>HD</sub>	Data Hold from Write End	0		0		0		ns
t <sub>LZWE</sub>	WE HIGH to Low Z <sup>[6]</sup>	3		3		3		ns
t <sub>HZWE</sub>	WE LOW to High Z <sup>[6, 7]</sup>		5		6		7	ns
t <sub>BW</sub>	Byte Enable to End of Write	7		8		9		ns

## Switching Waveforms

### Read Cycle No. 1<sup>[9, 10]</sup>



### Read Cycle No. 2 ( $\overline{OE}$ Controlled)<sup>[10, 11]</sup>

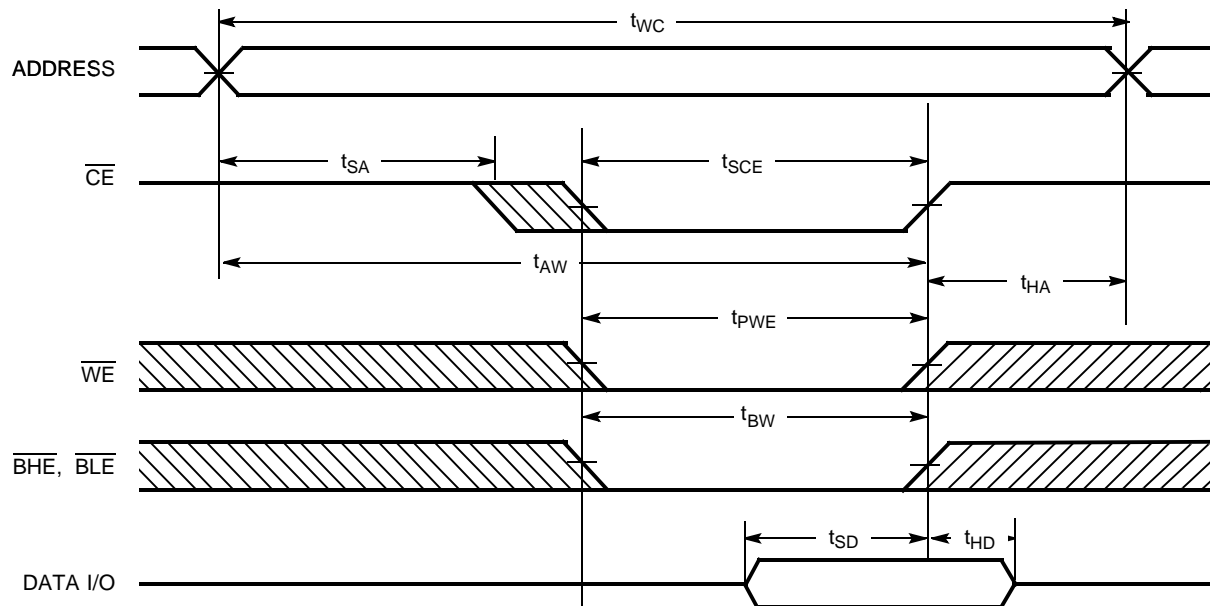


#### Notes:

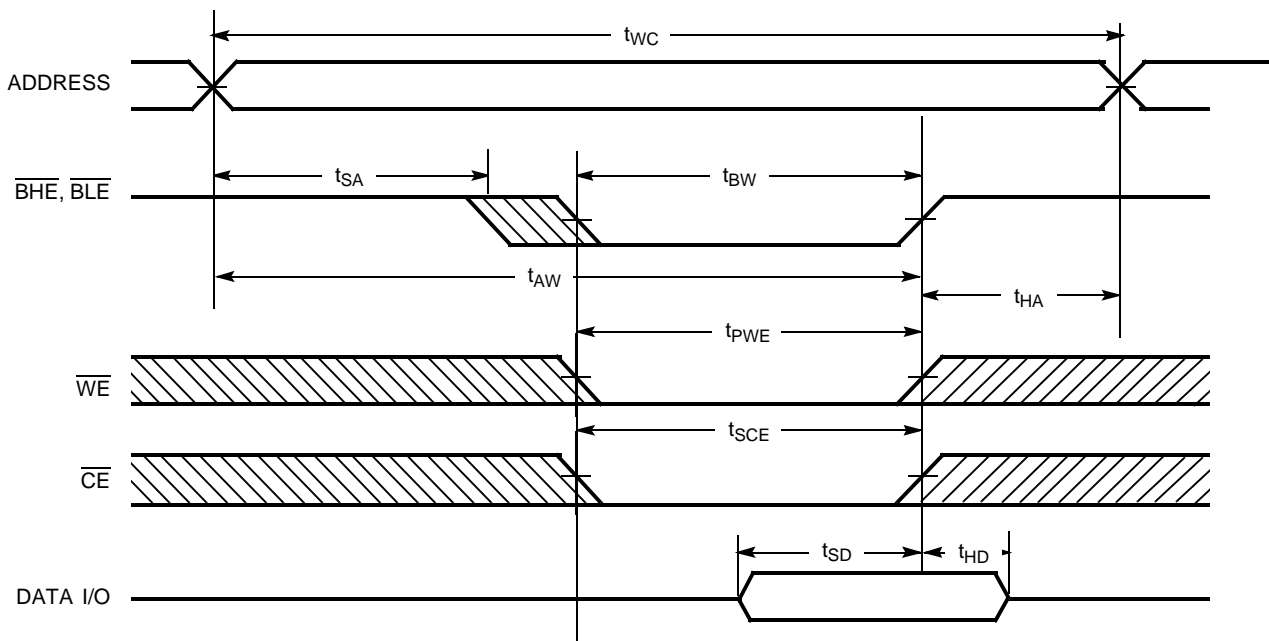
- The internal write time of the memory is defined by the overlap of  $\overline{CE}$  LOW,  $\overline{WE}$  LOW and  $\overline{BHE}$  /  $\overline{BLE}$  LOW.  $\overline{CE}$ ,  $\overline{WE}$  and  $\overline{BHE}$  /  $\overline{BLE}$  must be LOW to initiate a write, and the transition of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
- Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE}$ ,  $\overline{BHE}$  and/or  $\overline{BLE}$  =  $V_{IL}$ .
- $\overline{WE}$  is HIGH for read cycle.

## Switching Waveforms (continued)

### Write Cycle No. 1 ( $\overline{\text{CE}}$ Controlled)<sup>[12, 13]</sup>



### Write Cycle No. 2 ( $\overline{\text{BLE}}$ or $\overline{\text{BHE}}$ Controlled)

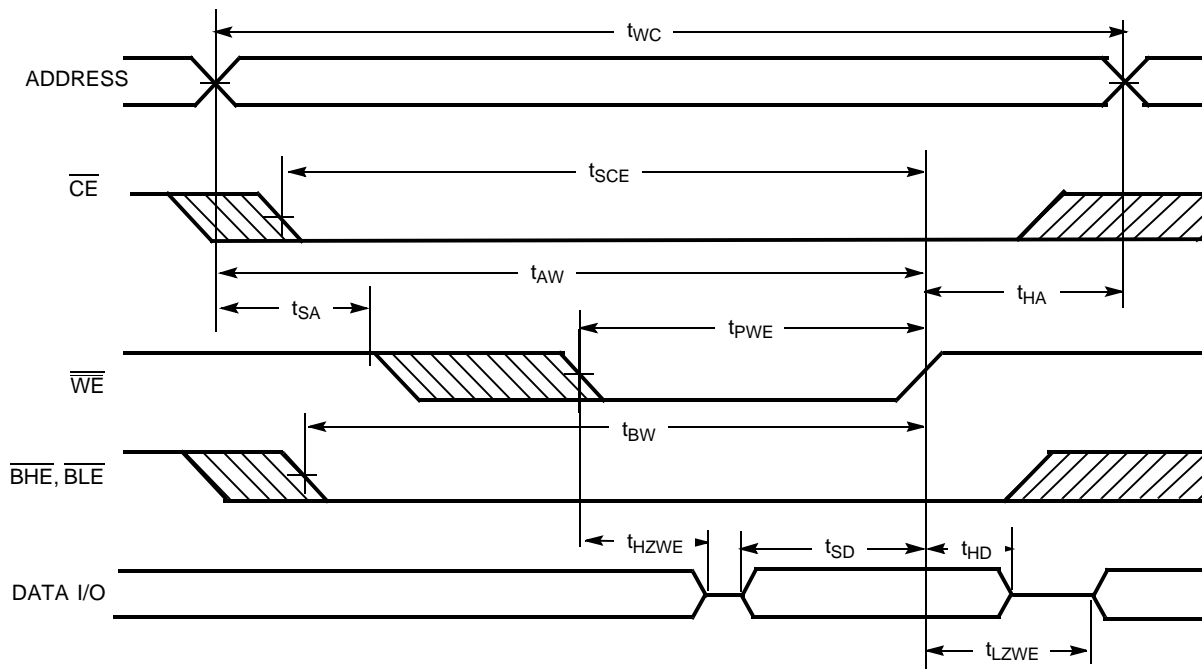


#### Notes:

11. Address valid prior to or coincident with  $\overline{\text{CE}}$  transition LOW.
12. Data I/O is high impedance if  $\overline{\text{OE}}$  or  $\overline{\text{BHE}}$  and/or  $\overline{\text{BLE}} = V_{IH}$ .
13. If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  going HIGH, the output remains in a high-impedance state.

## Switching Waveforms (continued)

Write Cycle No. 3 ( $\overline{\text{WE}}$  Controlled,  $\overline{\text{OE}}$  LOW)



## Truth Table

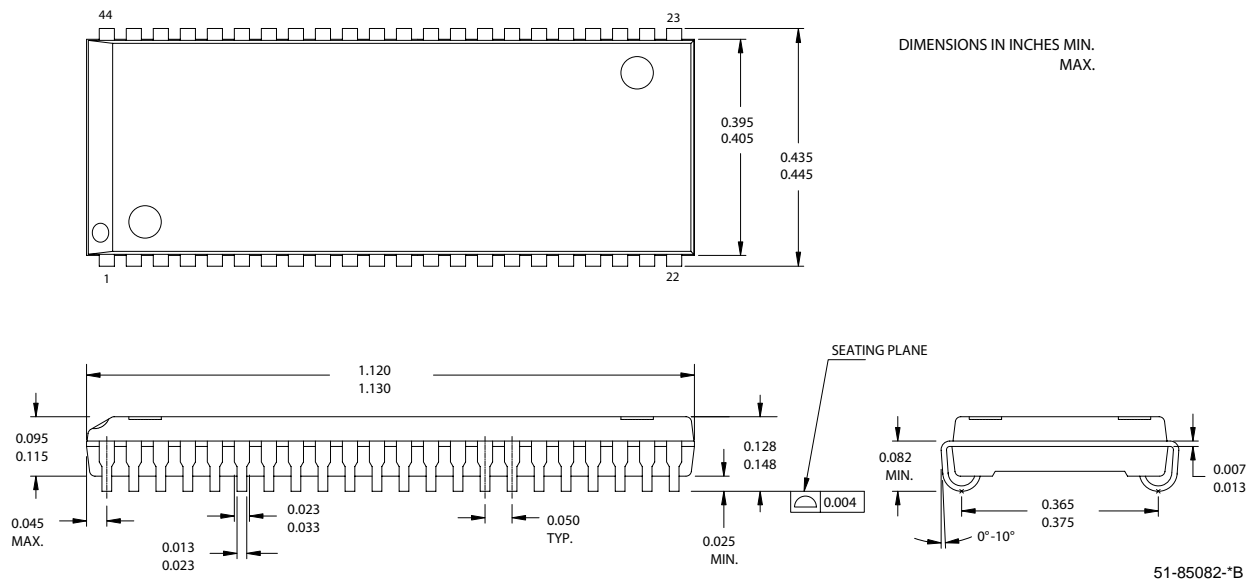
$\overline{\text{CE}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	$\overline{\text{BLE}}$	$\overline{\text{BHE}}$	I/O <sub>1</sub> –I/O <sub>8</sub>	I/O <sub>9</sub> –I/O <sub>16</sub>	Mode	Power
H	X	X	X	X	High Z	High Z	Power-Down	Standby ( $I_{\text{SB}}$ )
L	L	H	L	L	Data Out	Data Out	Read - All bits	Active ( $I_{\text{CC}}$ )
			L	H	Data Out	High Z	Read - Lower bits only	Active ( $I_{\text{CC}}$ )
			H	L	High Z	Data Out	Read - Upper bits only	Active ( $I_{\text{CC}}$ )
L	X	L	L	L	Data In	Data In	Write - All bits	Active ( $I_{\text{CC}}$ )
			L	H	Data In	High Z	Write - Lower bits only	Active ( $I_{\text{CC}}$ )
			H	L	High Z	Data In	Write - Upper bits only	Active ( $I_{\text{CC}}$ )
L	H	H	X	X	High Z	High Z	Selected, Outputs Disabled	Active ( $I_{\text{CC}}$ )
L	X	X	H	H	High Z	High Z	Selected, Outputs Disabled	Active ( $I_{\text{CC}}$ )

## Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C10211BN-10ZXC	51-85087	44-pin TSOP Type II	Commercial
12	CY7C1021BN-12VC	51-85082	44-pin (400-Mil) Molded SOJ	Commercial
	CY7C1021BN-12VXC		44-pin (400-Mil) Molded SOJ (Pb-Free)	
	CY7C1021BN-12ZC	51-85087	44-pin TSOP Type II	
	CY7C1021BN-12ZXC		44-pin TSOP Type II (Pb-Free)	
	CY7C1021BN-12VI	51-85082	44-pin (400-Mil) Molded SOJ	Industrial
	CY7C1021BN-12VXI		44-pin (400-Mil) Molded SOJ (Pb-Free)	
15	CY7C1021BN-15VC	51-85082	44-pin (400-Mil) Molded SOJ	Commercial
	CY7C1021BN-15VXC		44-pin (400-Mil) Molded SOJ (Pb-Free)	
	CY7C1021BNL-15VXC		44-pin (400-Mil) Molded SOJ (Pb-Free)	
	CY7C1021BN-15ZC	51-85087	44-pin TSOP Type II	
	CY7C1021BN-15ZXC		44-pin TSOP Type II (Pb-Free)	
	CY7C1021BNL-15ZC		44-pin TSOP Type II	
	CY7C1021BNL-15ZXC	51-85082	44-pin TSOP Type II (Pb-Free)	
	CY7C1021BN-15VI		44-pin (400-Mil) Molded SOJ	
	CY7C1021BN-15VXI		44-pin (400-Mil) Molded SOJ (Pb-Free)	
	CY7C1021BN-15ZI	51-85087	44-pin TSOP Type II	Industrial
	CY7C1021BNL-15ZI		44-pin TSOP Type II	
	CY7C1021BN-15ZXI		44-pin TSOP Type II (Pb-Free)	
	CY7C1021BNL-15ZXI	51-85087	44-pin TSOP Type II (Pb-Free)	
	CY7C1021BNL-15ZSXA		44-pin TSOP Type II (Pb-Free)	
	CY7C1021BN-15VXE	51-85082	44-pin (400-Mil) Molded SOJ (Pb-Free)	Automotive-E
	CY7C1021BN-15ZSXE	51-85087	44-pin TSOP Type II (Pb-Free)	

## Package Diagrams

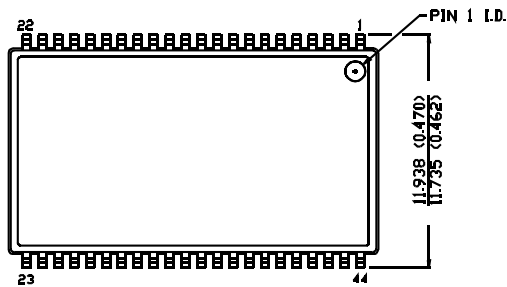
### 44-pin (400-Mil) Molded SOJ (51-85082)



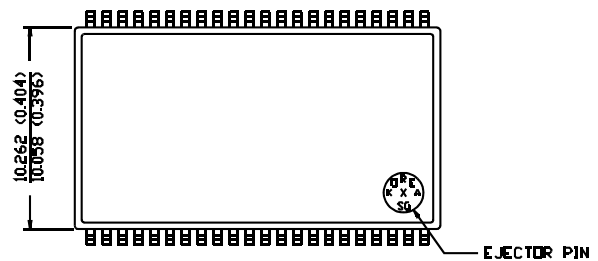
**Package Diagrams** (continued)

**44-Pin TSOP II (51-85087)**

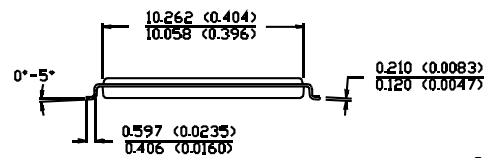
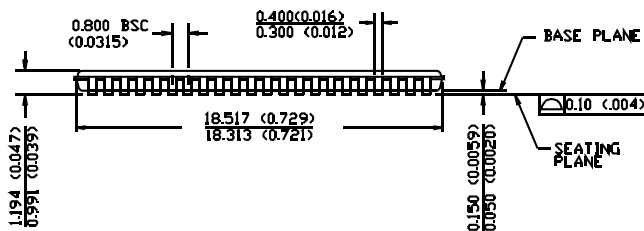
DIMENSION IN MM (INCH)  
MAX  
MIN.



**TOP VIEW**



**BOTTOM VIEW**



51-85087-\*A

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## Document History Page

Document Title: CY7C1021BN/CY7C10211BN (64K x 16) Static RAM Document Number: 001-06494				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	423877	See ECN	NXR	New Data Sheet
*A	505726	See ECN	NXR	Removed I <sub>OS</sub> parameter from DC Electrical Characteristics table. Added Automotive products Updated ordering Information table